30V N-Channel Enhancement Mode MOSFET

MTB55N03KSN3

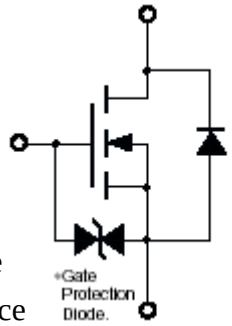
BV_{DSS}	30V
I_D @V_{GS}=10V, T_A=25°C	4.8A
$R_{DSON(TYP)}$@V_{GS}=10V, I_D=4.2A	35mΩ
$R_{DSON(TYP)}$@V_{GS}=4.5V, I_D=2A	50mΩ

Features

- Lower gate charge
- ESD protected gate
- Pb-free lead plating and Halogen-free package

Equivalent Circuit

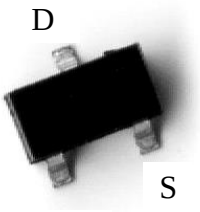
MTB55N03KSN3



G：Gate
S：Source
D：Drain

Outline

SOT-23



Ordering Information

Device	Package	Shipping
MTB55N03KSN3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products

Packing spec, T1 : 3000 pcs / tape & reel,7” reel

Product rank, zero for no rank products

Product name

Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	T_A=25°C, V_{GS}=10V	I_D	4.8	A
	T_A=70°C, V_{GS}=10V		3.8	
Pulsed Drain Current		I_{DM}	20 (Note 1 & 2)	
Power Dissipation	T_A=25°C	P_D	1.38 (Note 3)	W
	T_A=70°C		0.88 (Note 3)	
Operating Junction and Storage Temperature		Tj, Tstg	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient , max	$R_{\theta JA}$	90 *2	°C/W
Thermal Resistance, Junction to Case, max	$R_{\theta JC}$	70	

Note : 1. Pulse width limited by maximum junction temperature.
2. Duty cycle ≤ 1%.
3. Surface mounted on 1 in² copper pad of FR4 board, t≤10s; 270°C/W when mounted on min. copper pad.

Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	30	-	-	V	V_{GS}=0V, I_D=250μA
$V_{GS(th)}$	1	-	2.5		V_{DS}=V_{GS}, I_D=250μA
I_{GSS}	-	-	±10	μA	V_{GS}=±16V, V_{DS}=0V
I_{DSS}	-	-	1		V_{DS}=24V, V_{GS}=0V
	-	-	10		V_{DS}=24V, V_{GS}=0V, Tj=55°C
*$R_{DS(ON)}$ [1]	-	35	45	mΩ	I_D=4.2A, V_{GS}=10V
	-	50	65		I_D=2A, V_{GS}=4.5V
*G_{FS} [1]	-	5.5	-	S	V_{DS}=5V, I_D=3.5A
Dynamic					
Ciss	-	171	-	pF	V_{DS}=10V, V_{GS}=0V, f=1MHz
Coss	-	59	-		
Crss	-	35	-		
*$t_{d(ON)}$ [1] [2]	-	3.6	-	ns	V_{DS}=15V, I_D=4.2A, V_{GS}=10V, R_G=3Ω
*t_r [1] [2]	-	16	-		
*$t_{d(OFF)}$ [1] [2]	-	11.4	-		
*t_f [1] [2]	-	4.4	-		

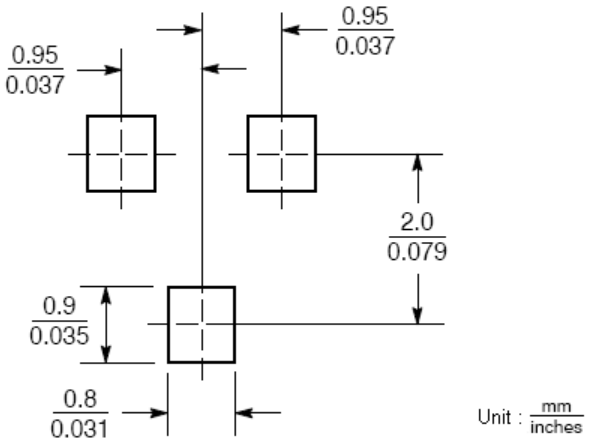
*Qg [1] [2]	-	2.7	-	nC	V_{DS}=15V, I_D=4.2A, V_{GS}=4.5V
*Qgs [1] [2]	-	0.9	-		
*Qgd [1] [2]	-	0.8	-		
Source-Drain Diode					
I_S	-	-	2	A	
I_{SM} [3]	-	-	8		
V_{SD} [1]	-	0.78	1	V	I_S=1A, V_{GS}=0V
trr [1]	-	6.6	-	ns	I_F=4.2A, dI_F/dt=100A/μs
Qrr [1]	-	2	-	nC	

[1] Pulse test : Pulse width≤300μs, Duty cycle≤2%

[2] Independent of operating temperature

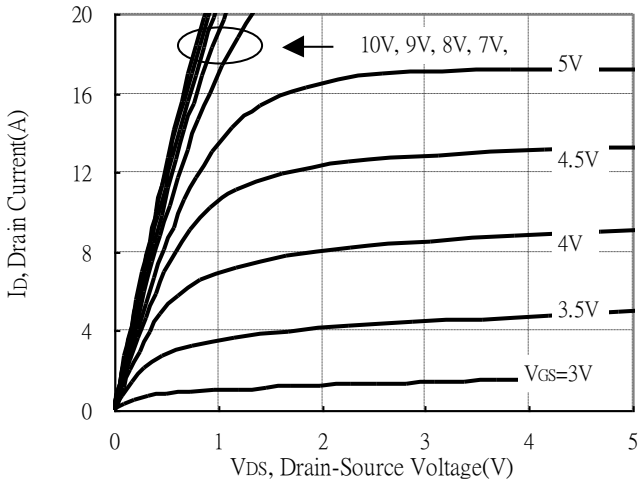
[3] Pulse width limited by maximum junction temperature

Recommended Soldering Footprint

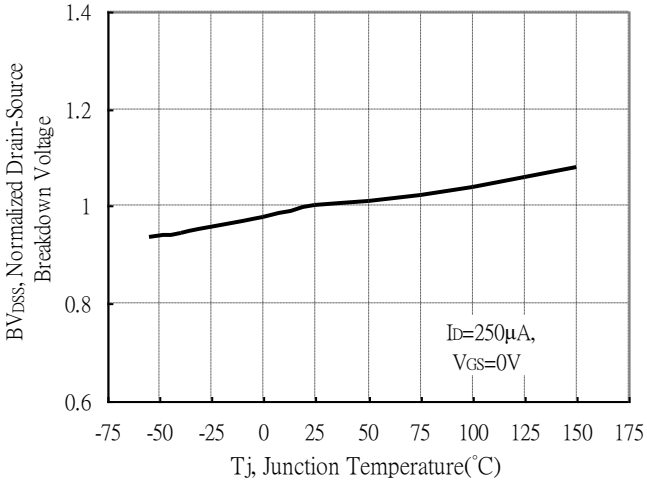


Typical Characteristics

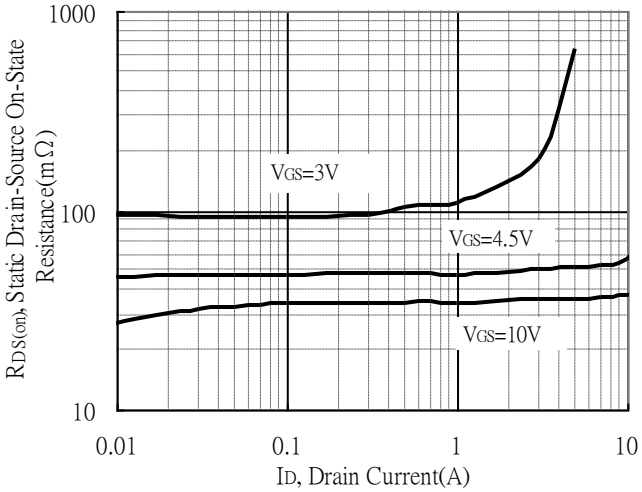
Typical Output Characteristics



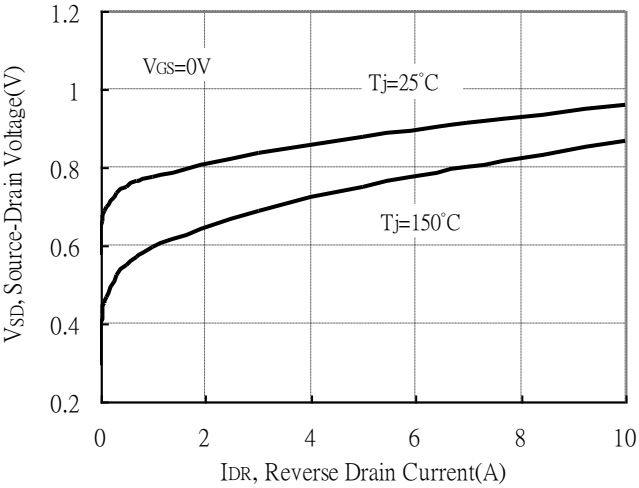
Brekdown Voltage vs Ambient Temperature



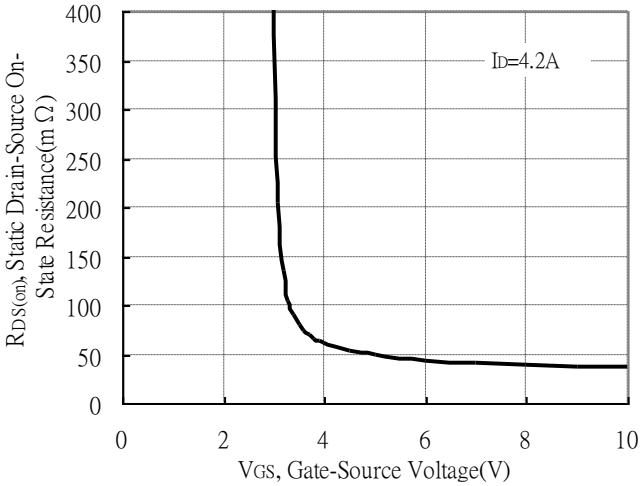
Static Drain-Source On-State resistance vs Drain Current



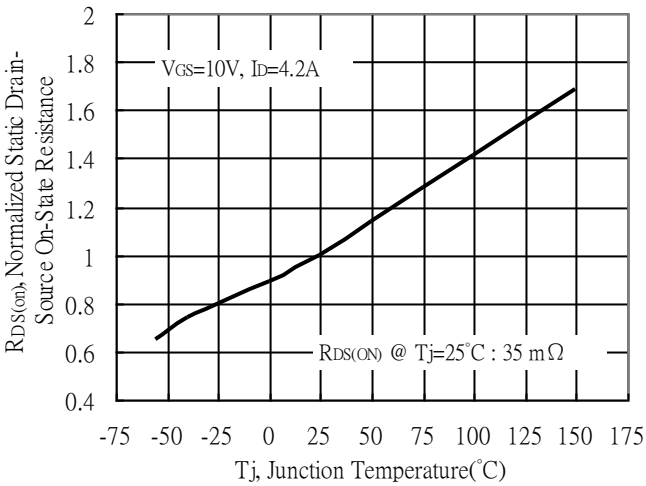
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

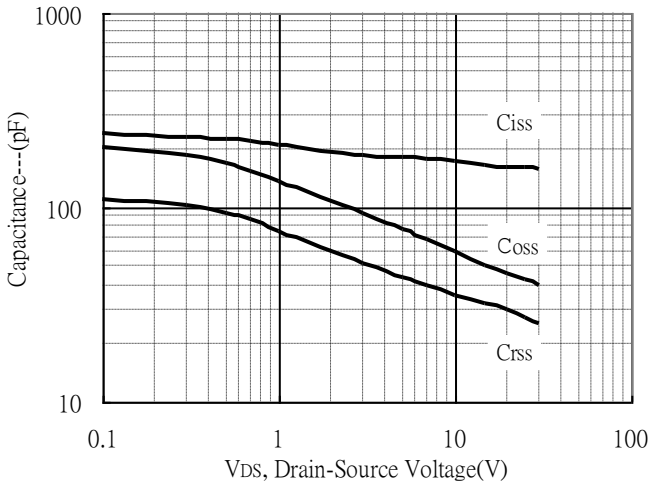


Drain-Source On-State Resistance vs Junction Tempearture

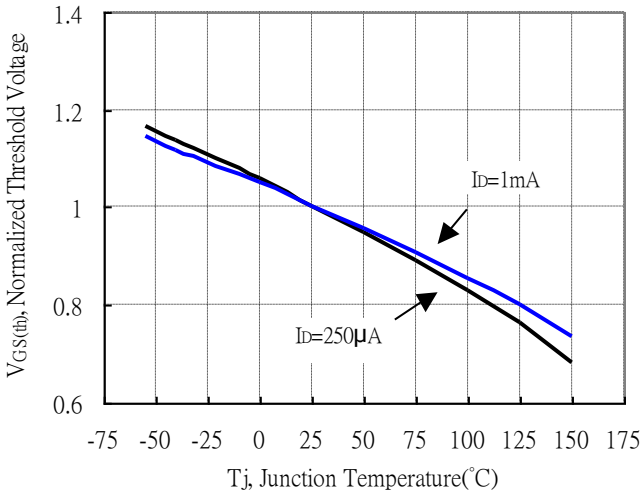


Typical Characteristics(Cont.)

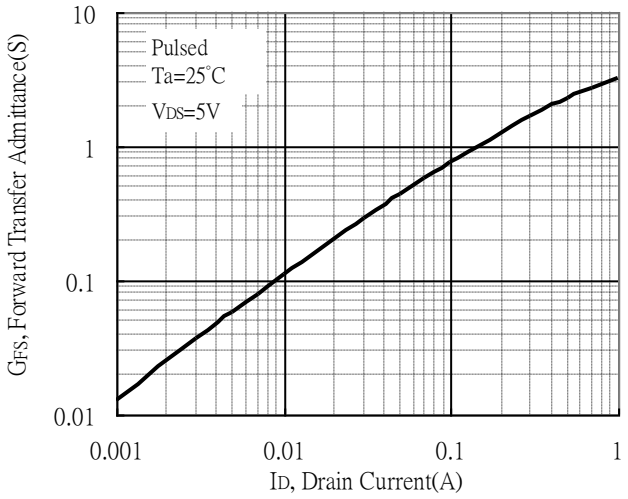
Capacitance vs Drain-to-Source Voltage



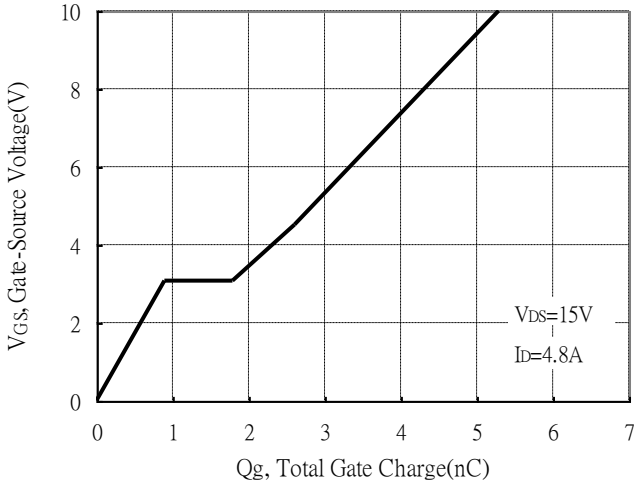
Threshold Voltage vs Junction Tempearture



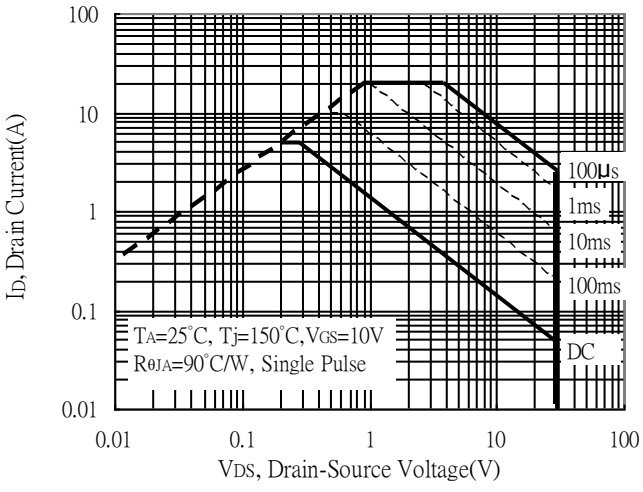
Forward Transfer Admittance vs Drain Current



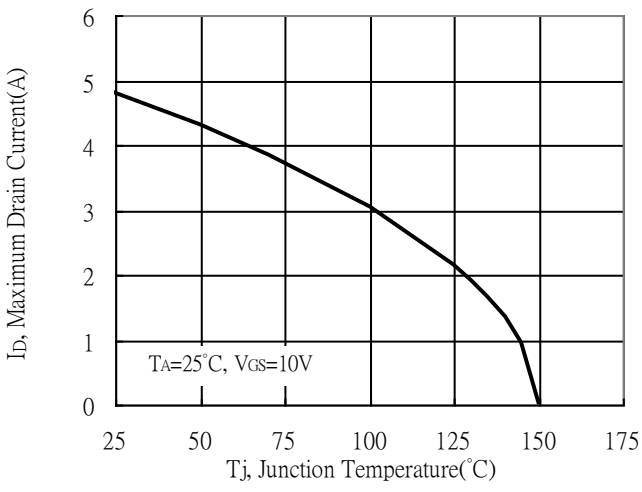
Gate Charge Characteristics



Maximum Safe Operating Area

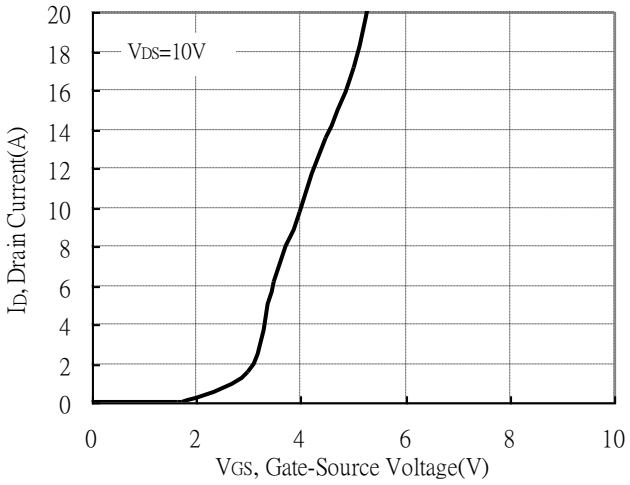


Maximum Drain Current vs JunctionTemperature

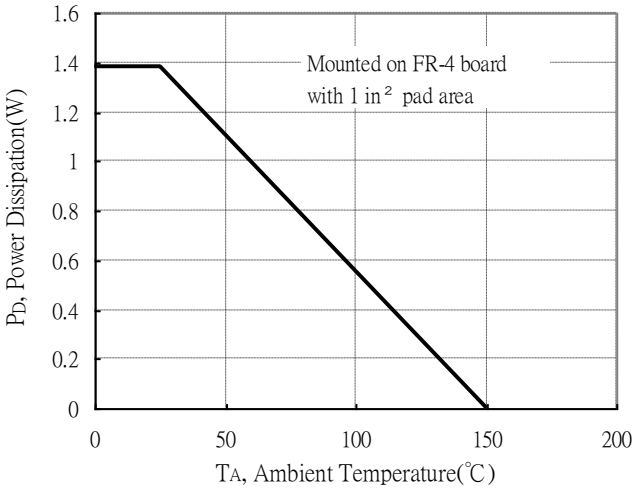


Typical Characteristics(Cont.)

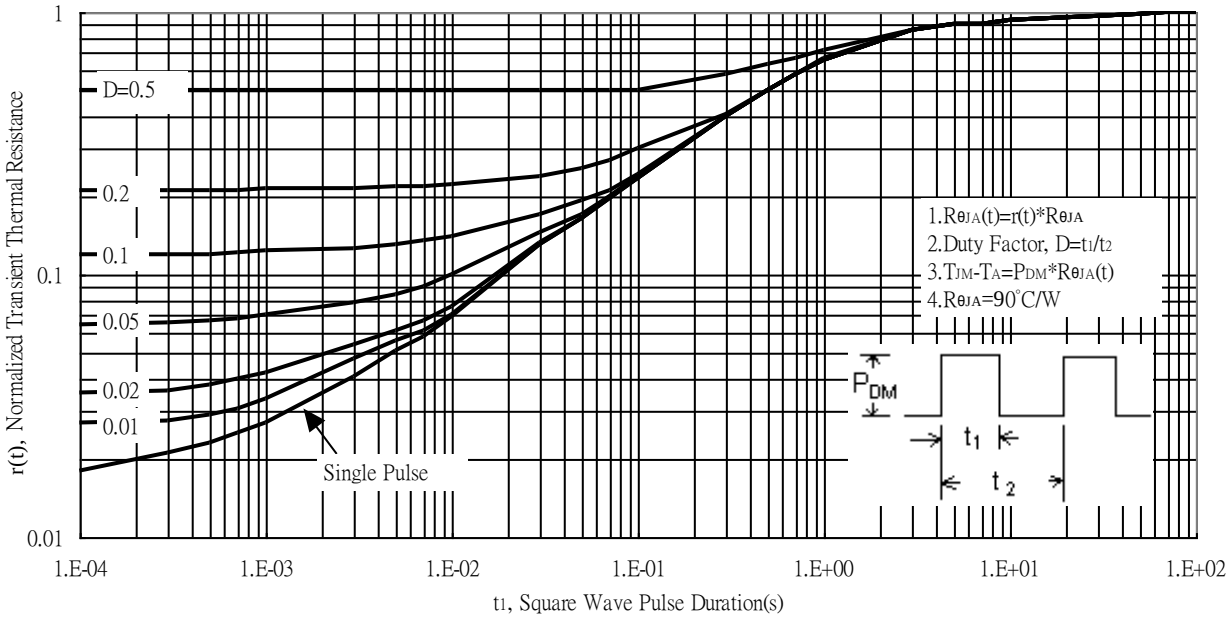
Typical Transfer Characteristics



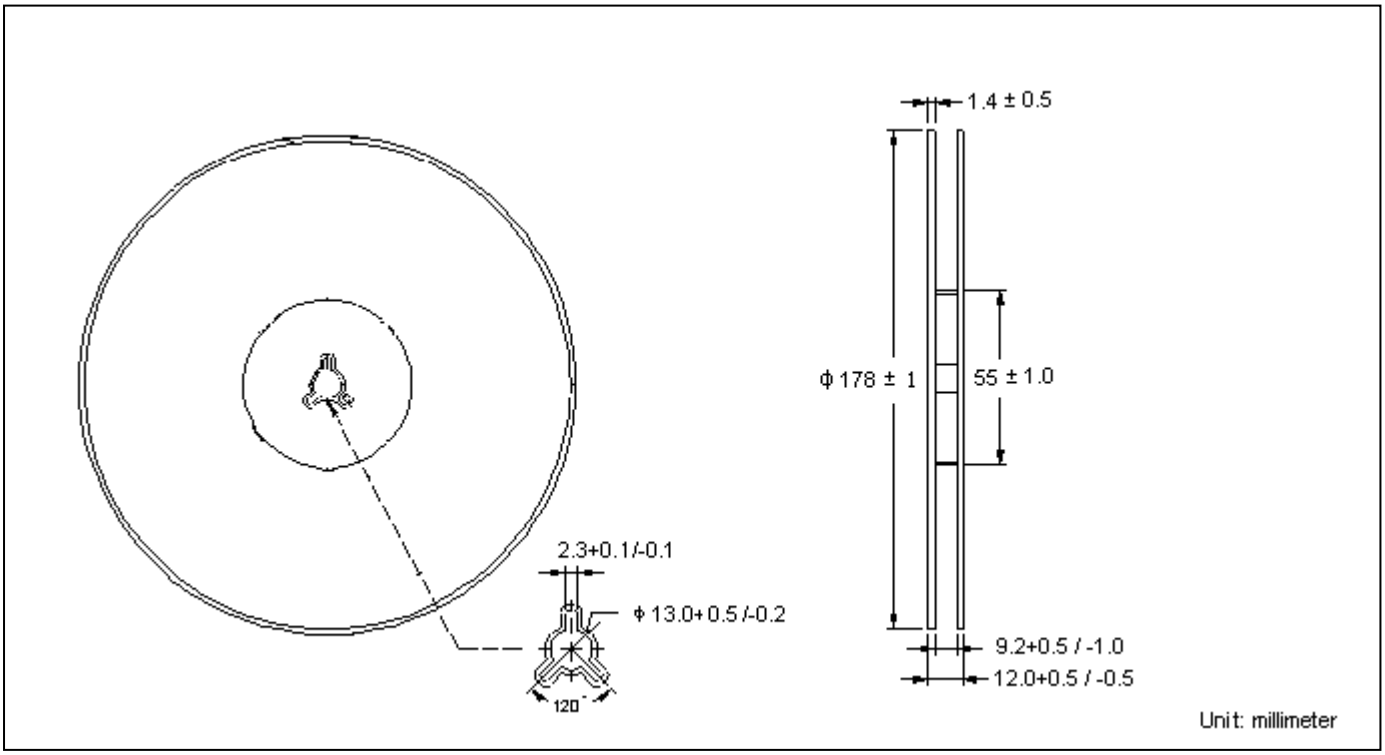
Power Derating Curve



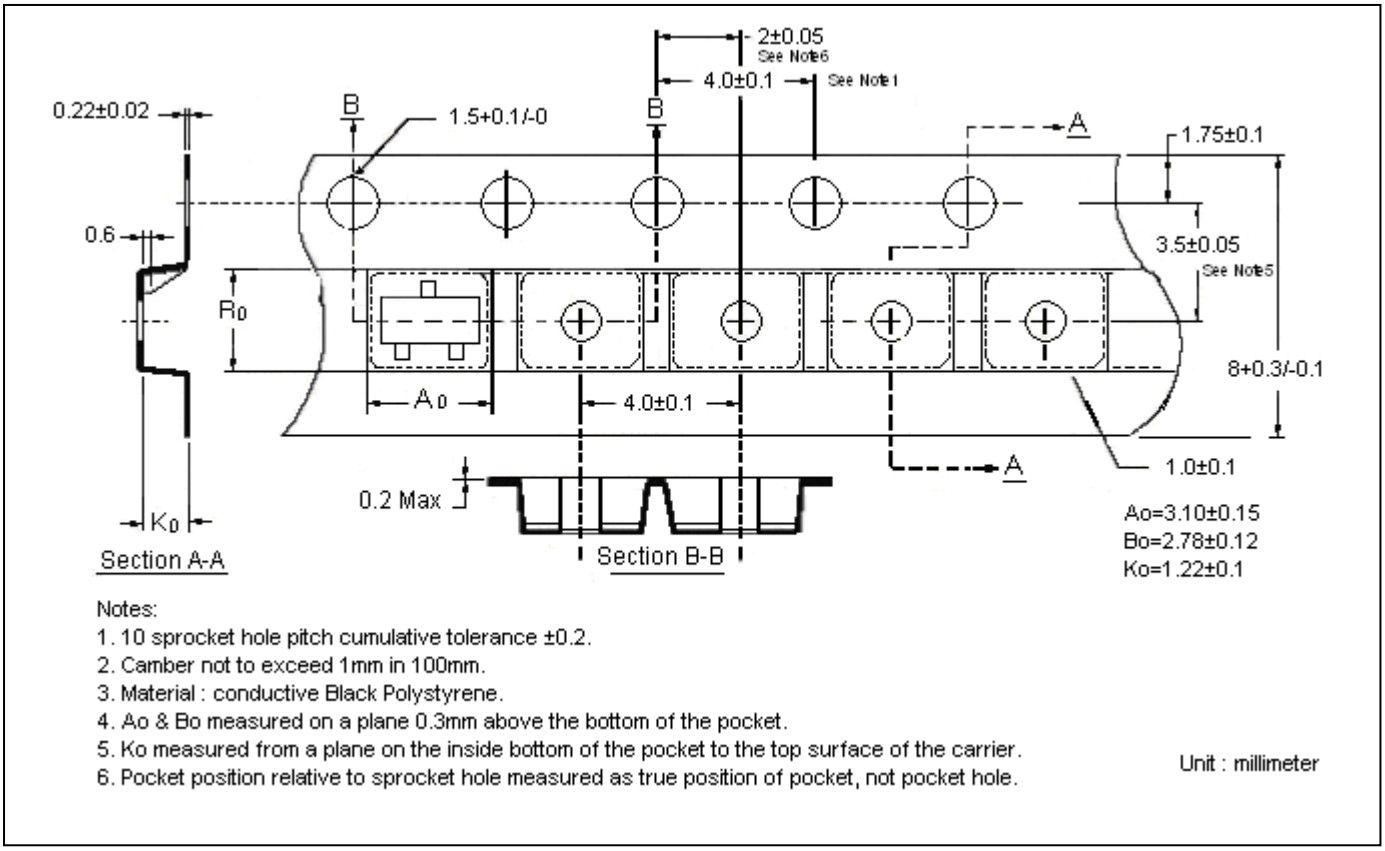
Transient Thermal Response Curves



Reel Dimension



Carrier Tape Dimension



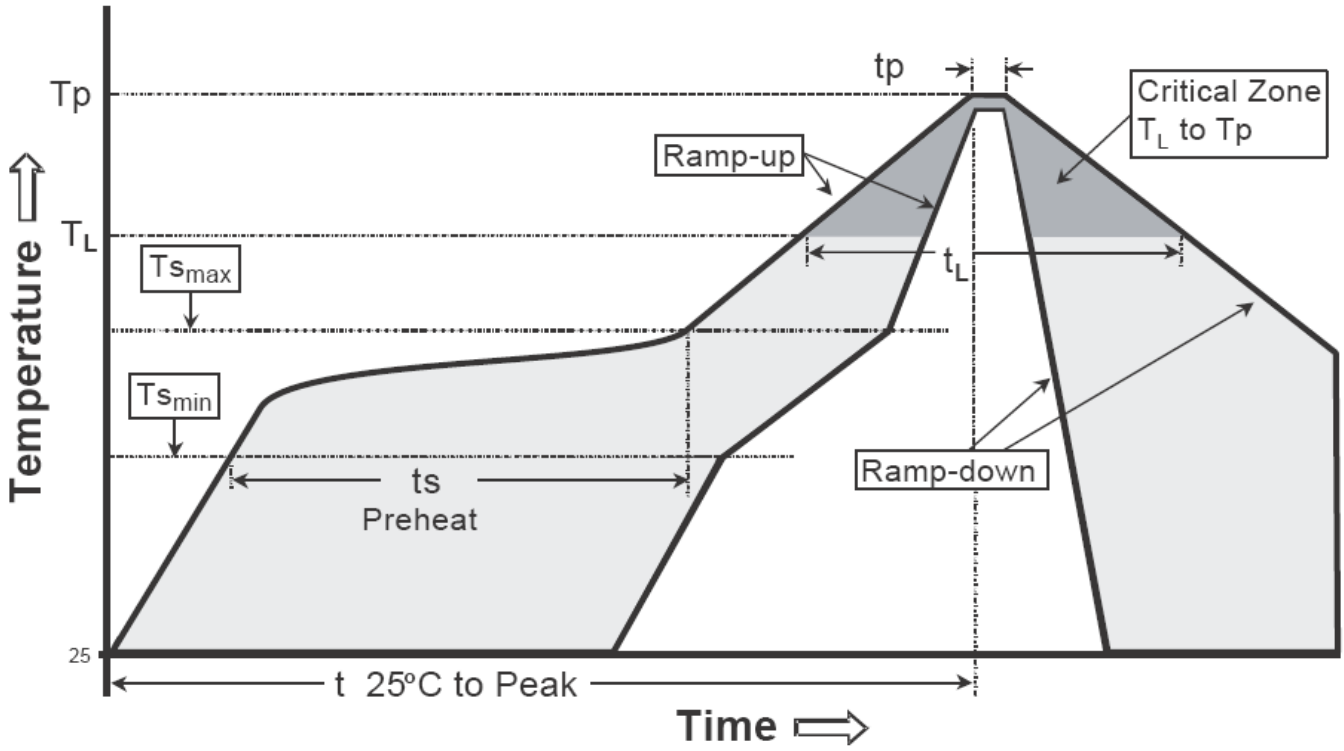
Notes:
1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

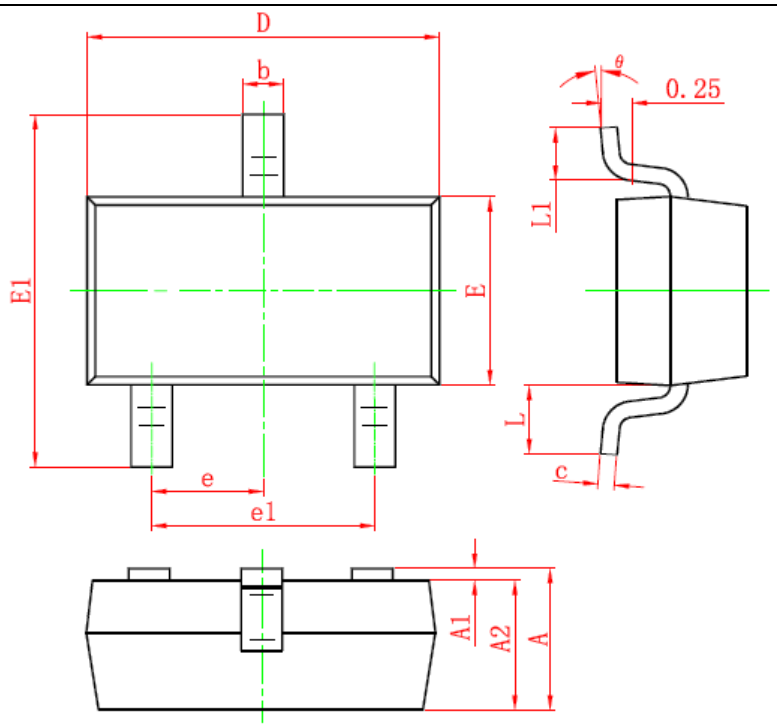
Recommended temperature profile for IR reflow



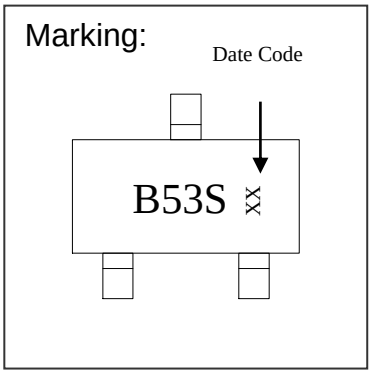
Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time($t_{s\ min}$ to $t_{s\ max}$)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension



Marking:



3-Lead SOT-23 Plastic
Surface Mounted Package
CYStek Package Code: N3

Style: Pin 1.Gate 2.Source 3.Drain

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045	E1	2.250	2.550	0.089	0.100
A1	0.000	0.100	0.000	0.004	e	0.950 TYP		0.037 TYP	
A2	0.900	1.050	0.035	0.041	e1	1.800	2.000	0.071	0.079
b	0.300	0.500	0.012	0.020	L	0.550 REF		0.022 REF	
c	0.080	0.150	0.003	0.006	L1	0.300	0.500	0.012	0.020
D	2.800	3.000	0.110	0.118	θ	0°	8°	0°	8°
E	1.200	1.400	0.047	0.055					

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.